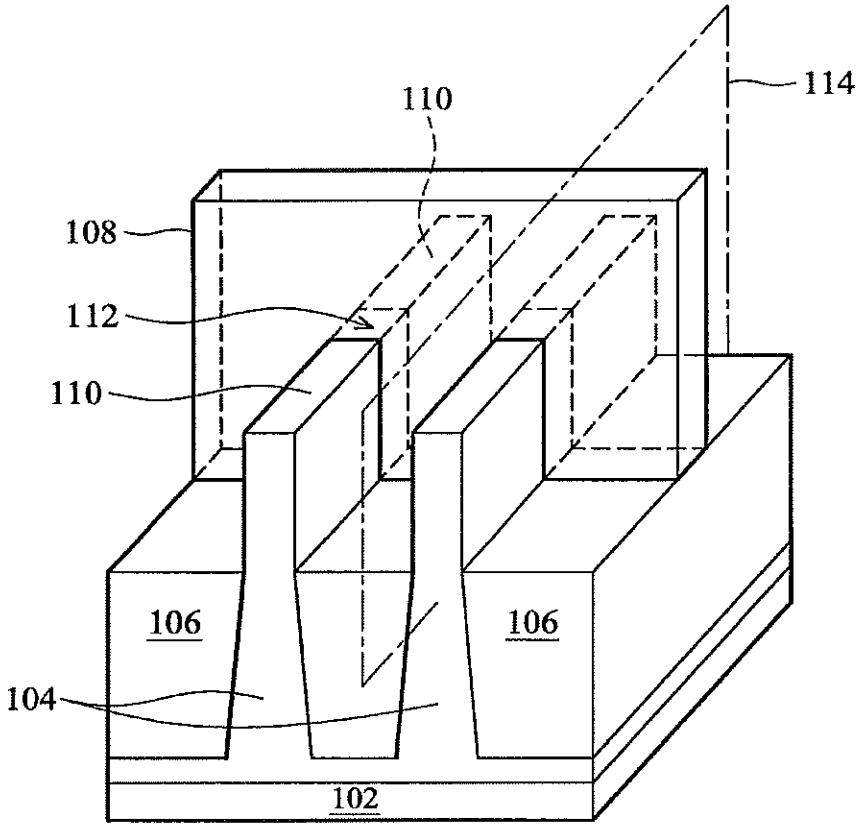


Fig. 1

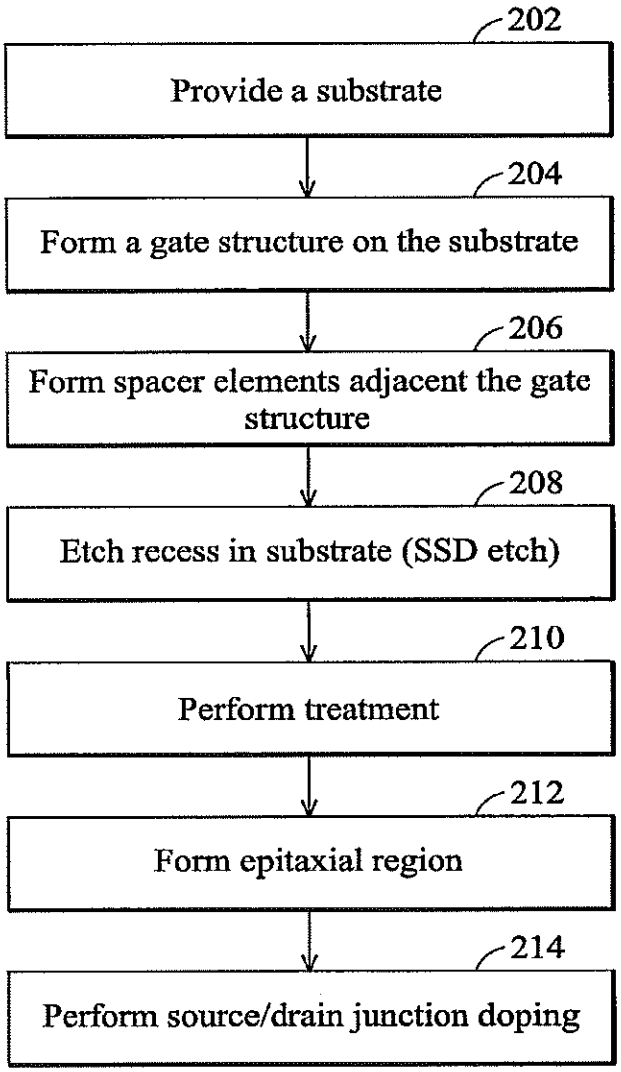

202
Provide a substrate
204
Form a gate structure on the substrate
206
Form spacer elements adjacent the gate structure
208
Etch recess in substrate (SSD etch)
210
Perform treatment
212
Form epitaxial region
214
Perform source/drain junction doping

Fig. 2

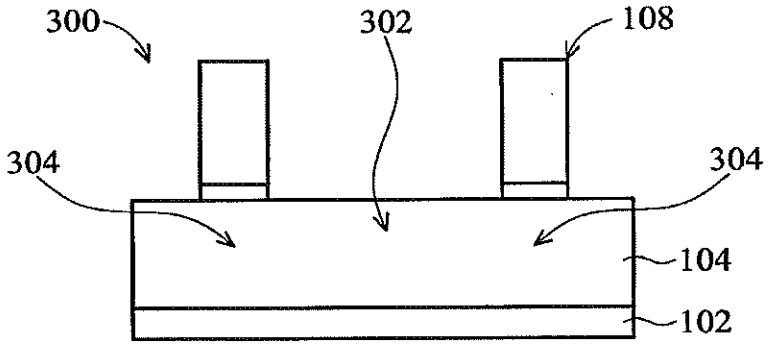


Fig. 3

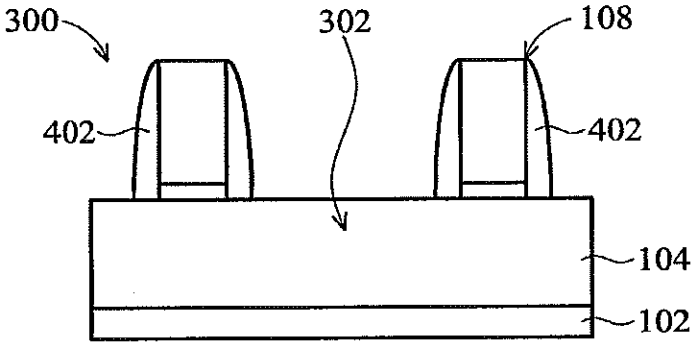


Fig. 4

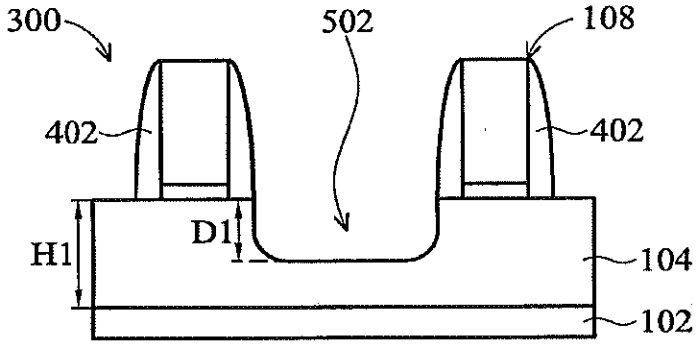


Fig. 5

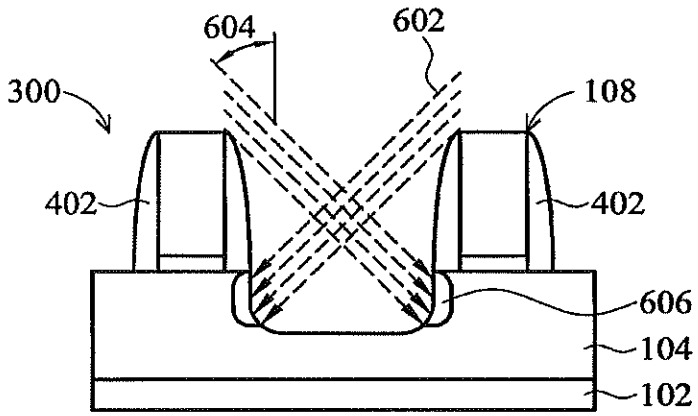


Fig. 6

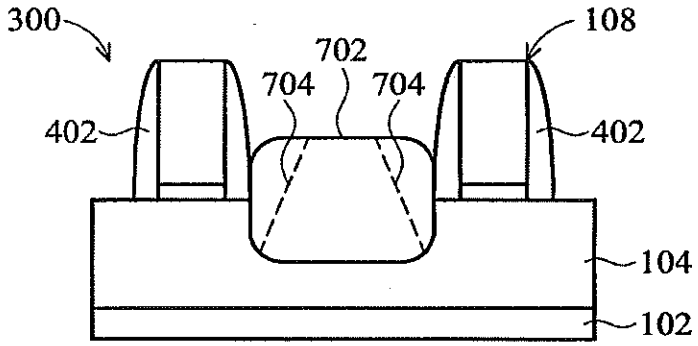


Fig. 7

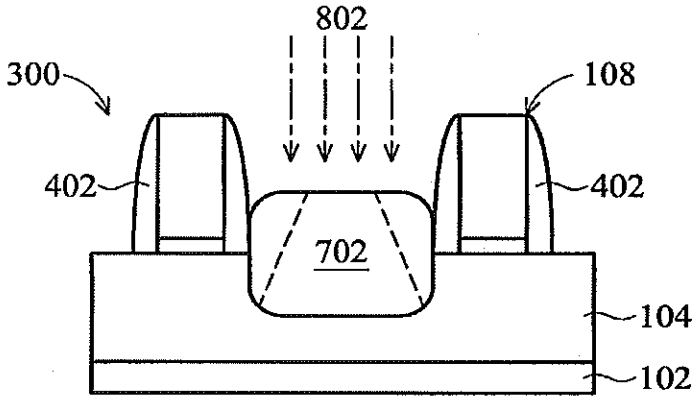


Fig. 8

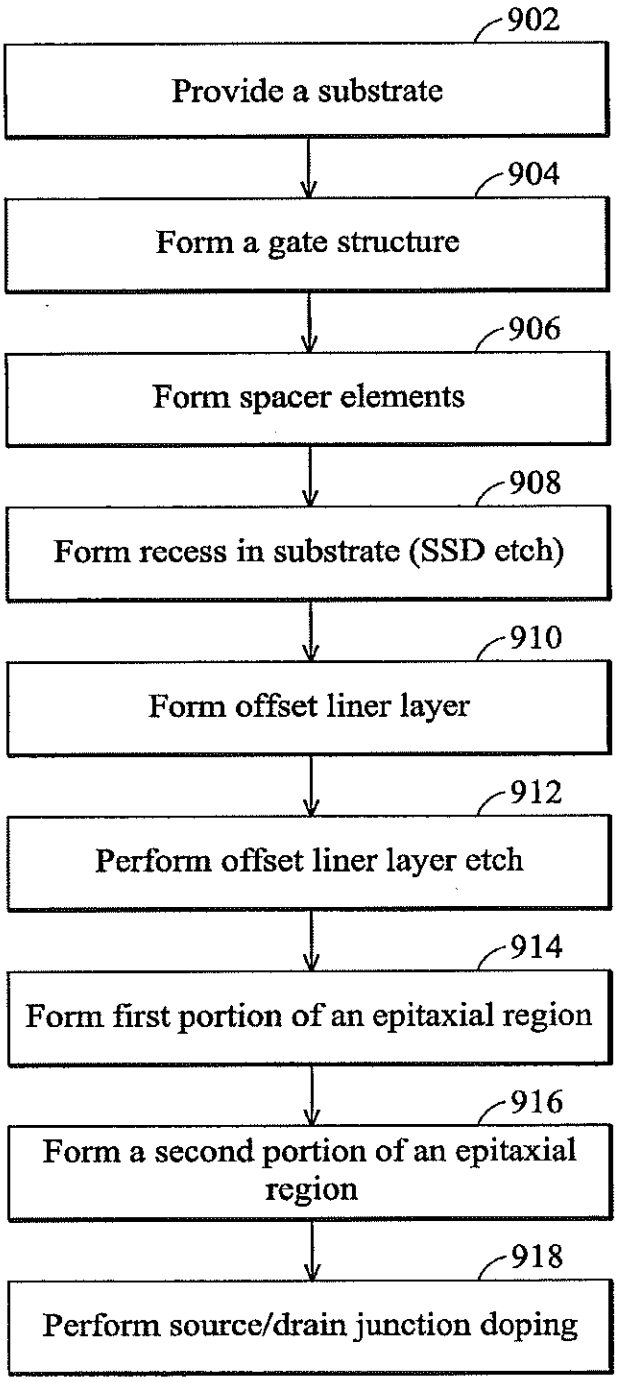

902
Provide a substrate
904
Form a gate structure
906
Form spacer elements
908
Form recess in substrate (SSD etch)
910
Form offset liner layer
912
Perform offset liner layer etch
914
Form first portion of an epitaxial region
916
Form a second portion of an epitaxial region
918
Perform source/drain junction doping

Fig. 9

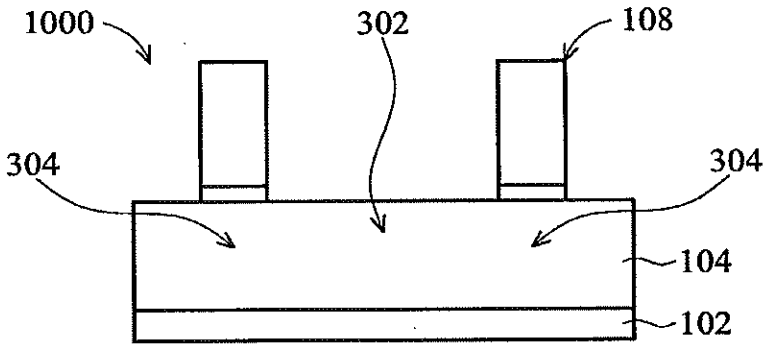


Fig. 10

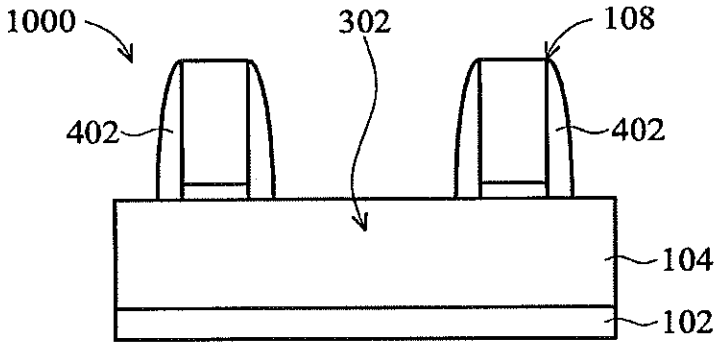


Fig. 11

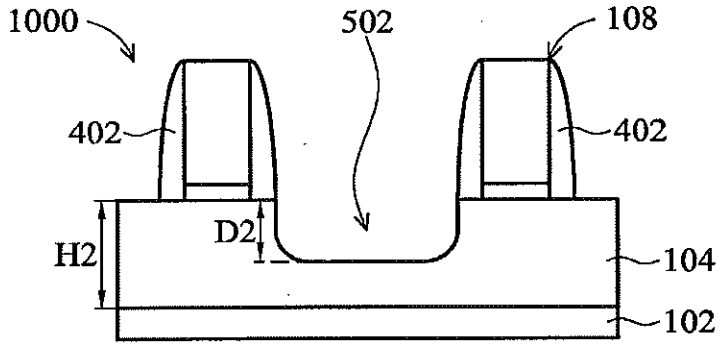


Fig. 12

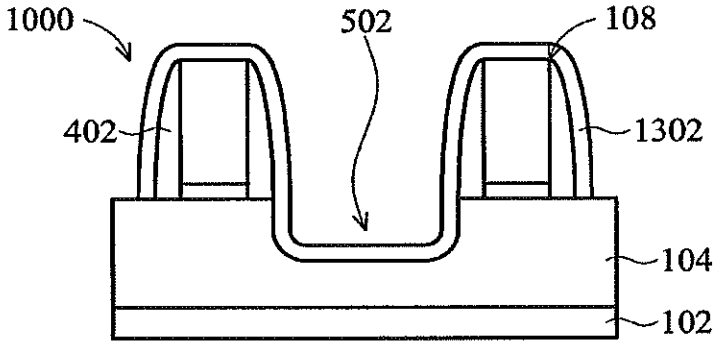


Fig. 13

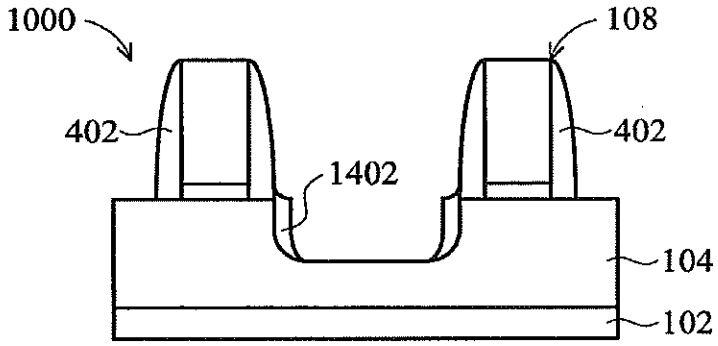


Fig. 14

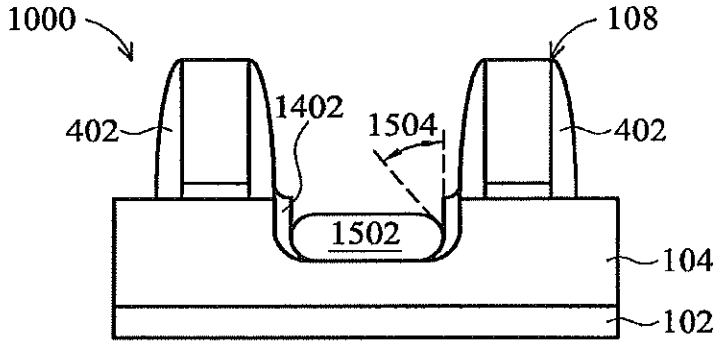


Fig. 15

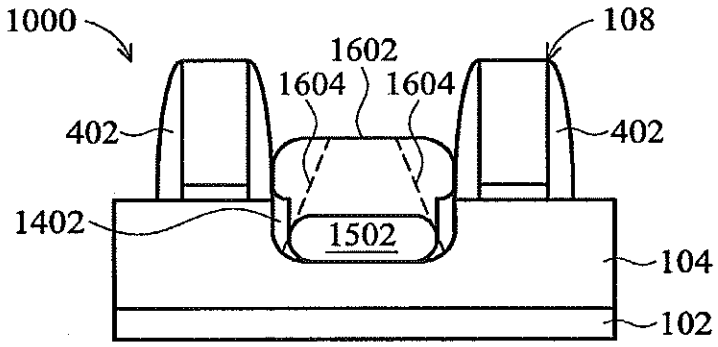


Fig. 16

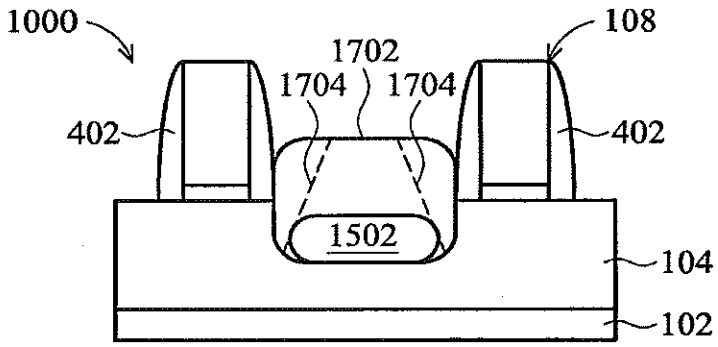


Fig. 17

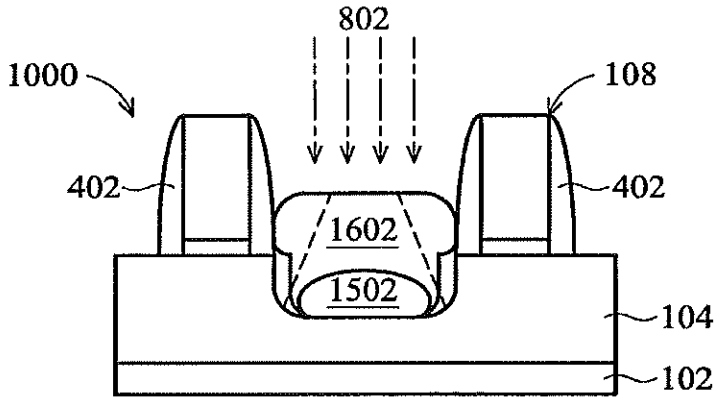


Fig. 18

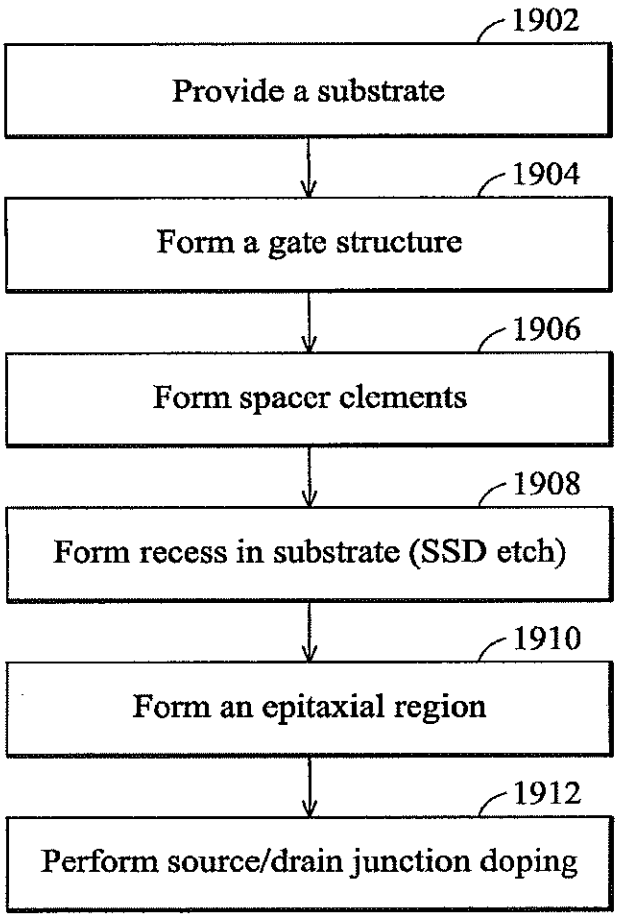

1902
Provide a substrate
1904
Form a gate structure
1906
Form spacer elements
1908
Form recess in substrate (SSD etch)
1910
Form an epitaxial region
1912
Perform source/drain junction doping

Fig. 19

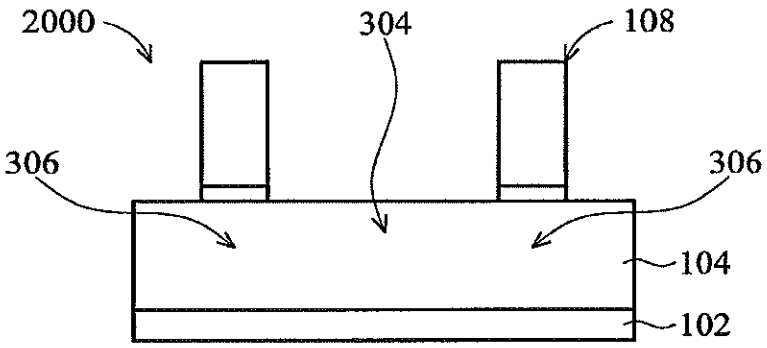


Fig. 20

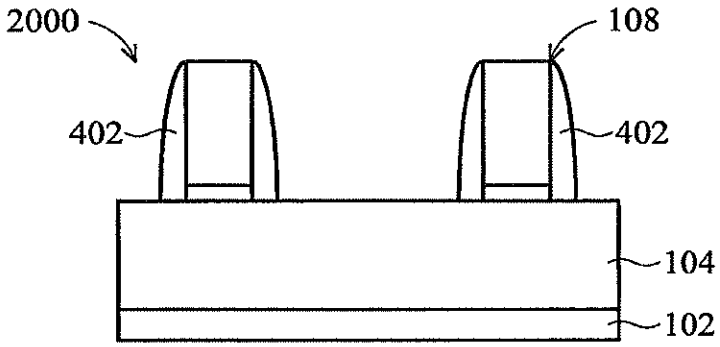


Fig. 21

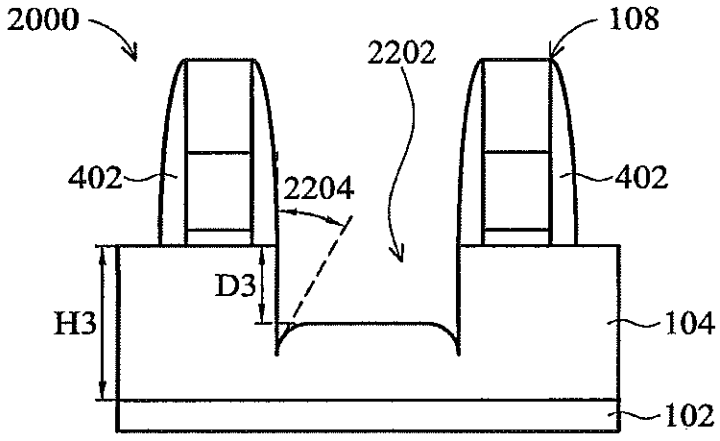


Fig. 22

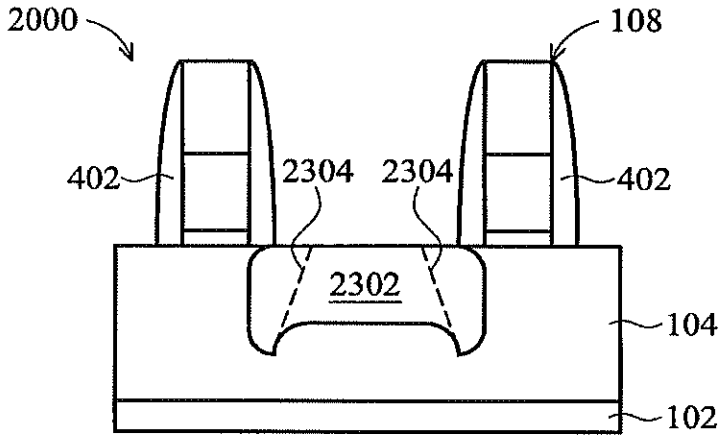

2000
108
402
2304
2304
402
2302
104
102

Fig. 23

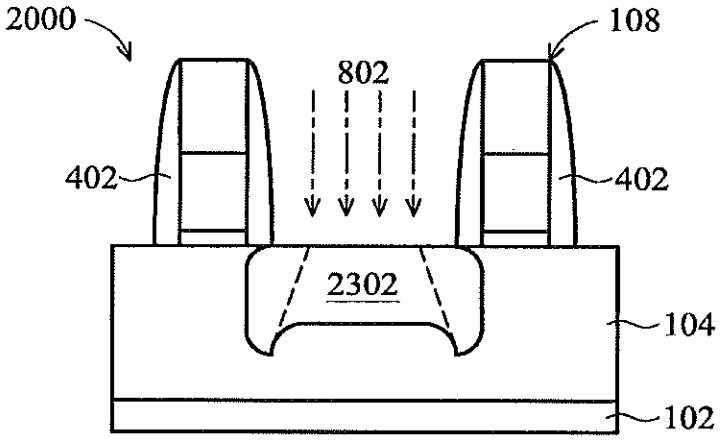

2000
108
802
402
402
2302
104
102

Fig. 24